

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	6718	"polysilicon gate"	USPAT	2001/07/06 10:55
2	BRS	L2	176	capacitor near10 1	USPAT	2001/07/06 11:00
3	BRS	L3	3322	depletion and inversion	USPAT	2001/07/06 11:01
4	BRS	L4	23	3 and 2	USPAT	2001/07/06 11:01
5	BRS	L5	136	("p-type" or "p-" or "p") near1 11	USPAT	2001/07/06 11:36
6	BRS	L6	8	2 and 5	USPAT	2001/07/06 11:36
7	BRS	L7	8	6 not 4	USPAT	2001/07/06 11:53
8	BRS	L8	96	"p-type" near1 11	USPAT	2001/07/06 11:53

	Type	Hits	Search Text
1	BRS	10678	variable near2 (capacitor or capacitance)
2	BRS	3322	inversion and depletion
3	BRS	88	(inversion and depletion) and (variable near2 (capacitor or capacitance))
4	BRS	42581	capacitor near5 (drain or source or gate or mosfet or fet or nmos or pmos)
5	BRS	47	(capacitor near5 (drain or source or gate or mosfet or fet or nmos or pmos)) and ((inversion and depletion) and (variable near2 (capacitor or capacitance)))